

RB160L-40

Diodes

# Schottky barrier diode

## RB160L-40

●Applications

High frequency rectification  
For switching power supply.

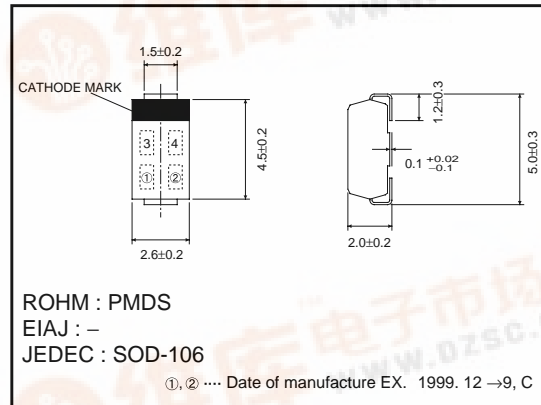
●Features

- 1) Compact power mold type (PMDS)
- 2) Low I<sub>r</sub>. (I<sub>r</sub>=5mA Typ.)
- 3) High reliability

●Construction

Silicon epitaxial Planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	40	V
DC reverse voltage	V <sub>R</sub>	40	V
Mean rectifying current *	I <sub>O</sub>	1	A
Peak forward surge current	I <sub>FSM</sub>	70	A
Junction temperature	T <sub>J</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-40~+125	°C

\*When mounted on a PCBs board

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	-	0.55	V	I <sub>F</sub> = 1.0A
Reverse current	I <sub>R</sub>	-	-	0.1	mA	V <sub>R</sub> = 40V

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● Electrical characteristic curves (Ta = 25°C)

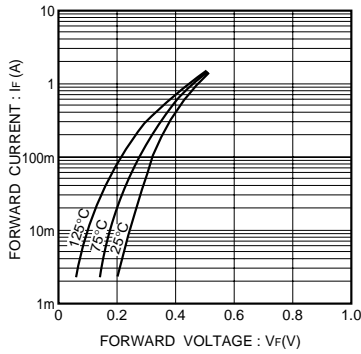


Fig. 1 Forward characteristics

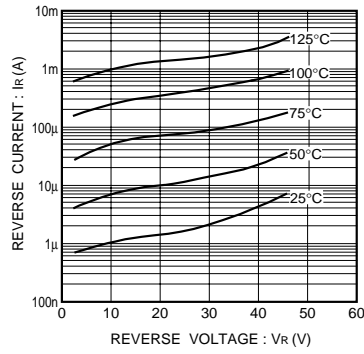


Fig. 2 Reverse characteristics

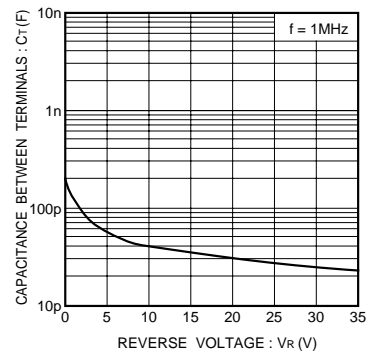


Fig. 3 Capacitance between terminals characteristics

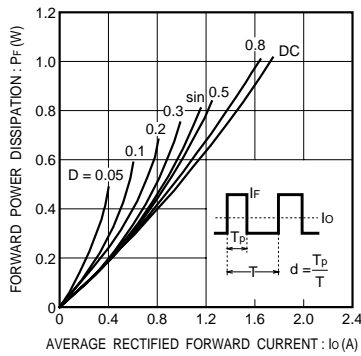


Fig. 4 Forward power dissipation characteristics

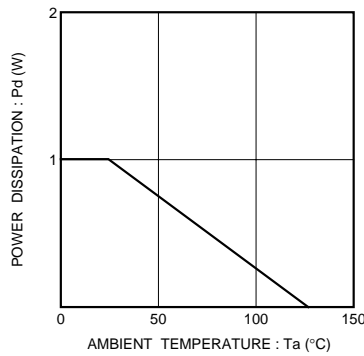


Fig. 5 Derating curve

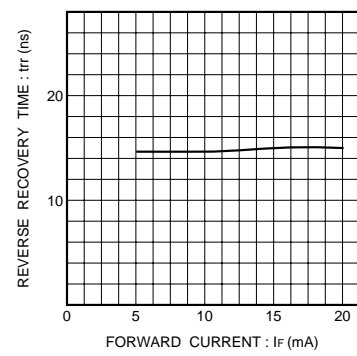


Fig. 6 Reverse recovery time characteristics